

High-voltage switching diodes Rev. 01 — 9 October 2009

Product data sheet

Product profile 1.

1.1 General description

High-voltage switching diodes, encapsulated in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Configuration	Package		Package
		NXP	JEDEC	configuration
BAS21W	single	SOT323	SC-70	very small
BAS21AW	dual common anode			
BAS21SW	dual series			

Low capacitance: $C_d \le 2 pF$

Reverse polarity protection

AEC-Q101 qualified

Voltage clamping

Very small SMD plastic package

1.2 Features

- High switching speed: $t_{rr} \le 50$ ns
- Low leakage current
- High reverse voltage: V_R ≤ 250 V

1.3 Applications

- High-speed switching
- General-purpose switching

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per diode						
l _F	forward current		<u>[1]</u> _	-	225	mA
I _R	reverse current	V _R = 200 V	-	-	100	nA
V _R	reverse voltage		-	-	250	V
t _{rr}	reverse recovery time		[2] _	-	50	ns

[1] Single diode loaded.

[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.



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2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
BAS21W			
1	anode		
2	not connected		3
3	cathode	1 2	1 2 006aaa764
BAS21AW			
1	cathode (diode 1)		
2	cathode (diode 2)		3
3	common anode		1 2 006aab0
BAS21SW			
1	anode (diode 1)		
2	cathode (diode 2)		3
3	cathode (diode 1), anode (diode 2)	1 2	

3. Ordering information

Table 4. Ordering information					
Type number	Package	Package			
	Name	Description	Version		
BAS21W	SC-70	plastic surface-mounted package; 3 leads	SOT323		
BAS21AW					
BAS21SW					

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4. Marking

Table 5. Marking codes	141
Type number	Marking code ^[1]
BAS21W	X4*
BAS21AW	X6*
BAS21SW	X5*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V _R	reverse voltage		-	250	V
l _F	forward current		<u>[1]</u> _	225	mA
			[2] _	125	mA
I _{FRM}	repetitive peak forward current		-	625	mA
I _{FSM} non-repetitive	non-repetitive peak forward	square wave	[3]		
	current	t _p = 1 μs	-	9	А
		t _p = 100 μs	-	3	А
		t _p = 10 ms	-	1.7	А
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[4]</u> _	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Single diode loaded.

[2] Double diode loaded.

[3] $T_i = 25 \,^{\circ}C$ prior to surge.

[4] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	625	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	300	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

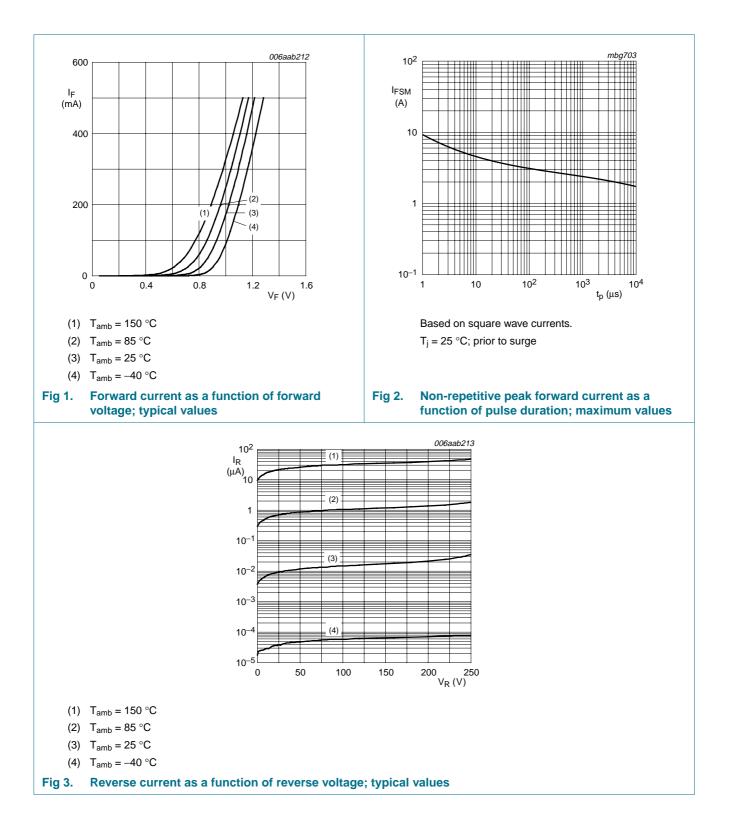
and						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode)					
V _F	forward voltage	I _F = 100 mA	-	-	1.0	V
		I _F = 200 mA	-	-	1.25	V
I _R	reverse current	V _R = 200 V	-	-	100	nA
		V_R = 200 V; T_j = 150 °C	-	-	100	μΑ
C _d	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	2	pF
t _{rr}	reverse recovery time		<u>[1]</u> -	-	50	ns

[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 $\Omega;$ measured at I_R = 1 mA.

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BAS21W series

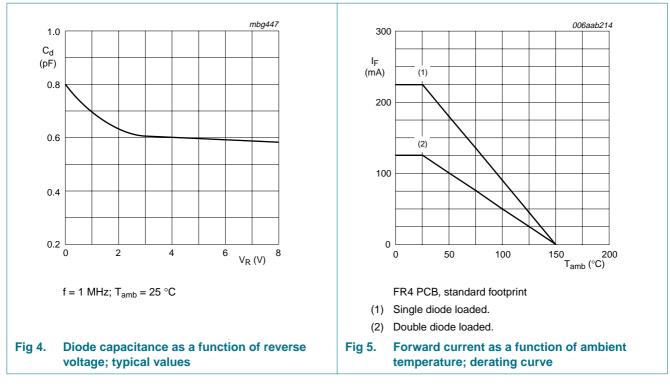
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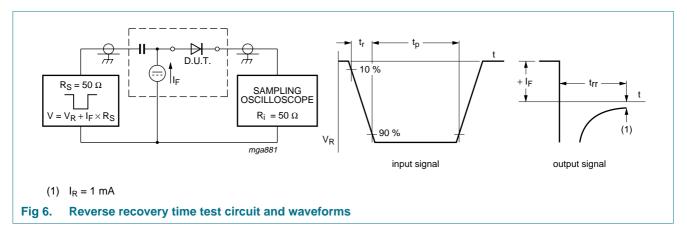
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8. Test information

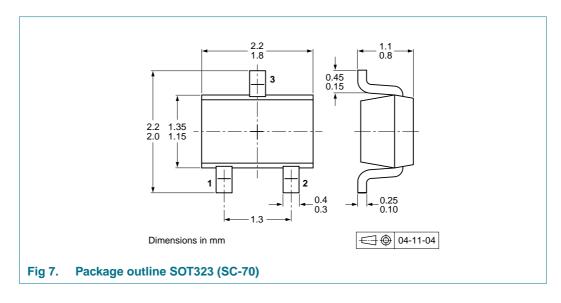


8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Packing information

Table 9. Packing methods

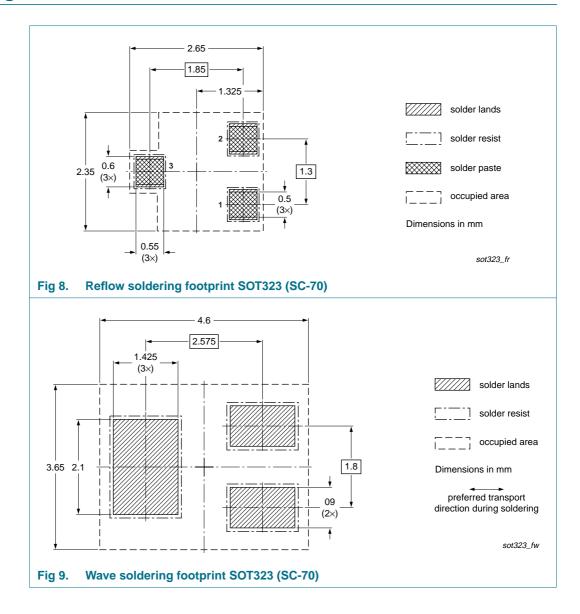
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity	
			3000	10000	
BAS21W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135	
BAS21AW					
BAS21SW					

[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 10. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS21W_SER_1	20091009	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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BAS21W_SER_1
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